

Title (en)

CAPACITOR AND A METHOD FOR PRODUCING A CAPACITOR

Title (de)

KONDENSATOR UND VERFAHREN ZUM HERSTELLEN EINES KONDENSATORS

Title (fr)

CONDENSATEUR ET SON PROCEDE DE FABRICATION

Publication

EP 1449245 A2 20040825 (DE)

Application

EP 02803774 A 20021114

Priority

- DE 10158798 A 20011130
- EP 0212786 W 20021114

Abstract (en)

[origin: WO03046974A2] The invention relates to a capacitor comprising a semiconductor substrate (114), in which a trench (112a, 112b), which is used to dope the substrate, is formed. A dielectric layer (118) covers the surface of the trench (112a, 112b) and an electrically conductive material (120a, 120b) is also located in the trench. In addition, a first contact structure (126) for electrically contacting the electrically conductive material (126) in the trench (112a, 112b) and a second contact structure (130) for electrically contacting the doped semiconductor substrate (114) are formed in the capacitor. The electrodes of the latter exhibit a low series resistance and said capacitor can be produced in a simple manner.

IPC 1-7

H01L 21/334; H01L 29/94

IPC 8 full level

H01L 21/334 (2006.01); **H01L 29/94** (2006.01)

CPC (source: EP US)

H01L 29/66181 (2013.01 - EP US); **H01L 29/945** (2013.01 - EP US)

Citation (search report)

See references of WO 03046974A2

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR IE IT LI LU MC NL PT SE SK TR

DOCDB simple family (publication)

WO 03046974 A2 20030605; **WO 03046974 A3 20031231**; AU 2002356602 A1 20030610; CN 100423211 C 20081001; CN 1596463 A 20050316; DE 10158798 A1 20030618; EP 1449245 A2 20040825; US 2005013090 A1 20050120; US 7030457 B2 20060418

DOCDB simple family (application)

EP 0212786 W 20021114; AU 2002356602 A 20021114; CN 02823791 A 20021114; DE 10158798 A 20011130; EP 02803774 A 20021114; US 85374004 A 20040525